SUMMARY In this paper, the research advances in silicon based millimeter wave and THz ICs in the State Key Laboratory of Millimeter Waves is reviewed, which consists of millimeter wave amplifiers, mixers, oscillators at Q, V and W and D band based on CMOS technology, and several research approaches of THz passive ICs including cavity and filter structures using SIW-like (Substrate Integrated Waveguide-like) guided wave structures based on CMOS and MEMs process. The design and performance of these components and devices are presented.

key words: millimeter wave, THz, amplifiers, mixers, oscillators, substrate integrated waveguide (SIW), half mode SIW (HMSIW)

1. Introduction

With the rapid advances of silicon based process in recent years, the characteristic frequency $f_T$ and $f_{max}$ have grown into millimeter wave and even THz band. In the next ten years, it could be predicted that the silicon based CMOS ICs will be practicable in millimeter wave band, and partially applicable in sub-millimeter or terahertz band when $f_{max}$ exceeds 1 THz [1]. The reported silicon based millimeter wave IC ranges from 30 GHz to 650 GHz in recent years [2]–[6]. In this paper, we will review the recent advances in silicon based millimeter wave active ICs and THz passive ICs developed in the State Key Laboratory of Millimeter Waves, Southeast University, Nanjing, China.

2. CMOS Millimeter Wave ICs

This section reviews several millimeter wave circuits based on CMOS technology developed in SKLMMW, including amplifiers, mixers, oscillators at Q, V and W and D band.

2.1 Q/V/W-Band CMOS Amplifiers

In the design of millimeter wave CMOS amplifiers, several kind of amplifiers are designed and tested by using IBM 90 nm CMOS technology, including gain stage amplifiers, power amplifiers, and low noise amplifiers at Q, V and W-band. Common source and cascode structure are employed in the design of these amplifiers.

Figure 1 shows a three-stage CMOS low noise amplifier, which has a measured gain of more than 15 dB at 45–56 GHz.

Figure 2 shows another three-stage CMOS power amplifier, which has a measured gain of more than 15 dB at 45–56 GHz.

Figure 3 shows another two-stage cascode amplifier, which has a measured gain of more than 15 dB at 45–52 GHz.

Figure 6 shows another three-stage cascode amplifier, which has a measured gain of more than 20 dB at 45–60 GHz, and the highest gain exceeds 90 dB. The authors are with the State Key Laboratory of Millimeter Waves, School of Information Science and Engineering, Southeast University, Nanjing, 210096, P. R. China.

††The author is with the Institute of RF- & OE-ICs, School of Information Science and Engineering, Southeast University, Nanjing, 210096, P. R. China.

†††The author is with the Poly-Grames Research Center, Ecole Polytechnique, University of Montreal, QC H3C 3J7, Canada.

a) E-mail: jxchen@emfield.org

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25 dB.

Figure 7–Fig. 9 shows three W-band CMOS gain amplifiers. Figure 7 shows a two-stage cascode amplifier, which has a measure gain of more than 5 dB at 90–107 GHz. Figure 8 is a two-stage common source amplifier, which has a measure gain of more than 5 dB at 90–106 GHz. Figure 9 shows a three-stage common source amplifier, which has a measure gain of more than 10 dB at 95–102 GHz, and the highest gain exceeds 12 dB.

2.2 V/W-Band CMOS Mixers

In the design of millimeter wave CMOS mixers, fundamental and sub-harmonic scheme are employed in circuit topology, four mixers are designed and tested at V-band and W-band by using IBM 90 nm CMOS technology.

Figure 10 and Fig. 11 show two fundamental CMOS mixer at V-band and W-band, using same structure. These mixers employ resistive mixing topology. The LO port is injected at the gate of n-FET and RF is injected at the drain of n-FET, the IF signal is filtered by a LC network at the drain output. The V-band fundamental mixer, as shown in Fig. 10, has a conversion loss of less than 10 dB at 50–75 GHz. The W-band fundamental mixer, as shown in Fig. 11, has a conversion loss of less than 14 dB at 75–110 GHz.

Figure 12 and Fig. 13 show another two CMOS mixer at V-band using sub-harmonic scheme. In Fig. 12, the LO port is injected at the gate of n-FET and RF is injected at the drain, the IF signal is generated by the mixing of LO harmonic and RF signal, and it is filtered by a LC network at the drain output. In Fig. 13, diode pair is used for sub-harmonic mixing, and short/open stubs is used to suppress the unwanted signals. These two mixers has a conversion loss of less than 15 dB at 50–75 GHz.

2.3 V/W/D-Band CMOS Oscillators

In the design of millimeter wave CMOS oscillators, cross-coupled transistors are implemented as the oscillation core, push-push structure is used to get higher output frequency. Two voltage-controlled oscillators (VCO) at V-band and W-band and a fixed frequency oscillator at D-band are designed and tested by using IBM 90 nm CMOS technology.

Figure 14 shows a V-band CMOS VCO using push-
push structure, the output frequency is tune by a tunable capacitor at resonance network. This VCO has a measured tuning range of 59–69 GHz, output power of $-10\text{ dBm}$, and phase noise of $-103 \text{ dBc@10 MHz offset}$.

Figure 15 shows a W-band CMOS VCO using the similar structure with frequency optimized at W-band. It has a measured tuning range of 93–104 GHz, output power of $-20\text{ dBm}$, and phase noise of $-93 \text{ dBc@10 MHz offset}$.

Figure 16 shows a D-band CMOS oscillator using push-push structure and a fixed resonance network due to the lack of tunable devices at D-band. This oscillator is measured with a D-band probe from Picoprobe, and a down-converter form Farran technology. The measure oscillation frequency is around 160.9 GHz, the output power is around $-25.6\text{ dBm}$. Figure 17 shows the measured spectrum.

3. Silicon Based THz ICs

This section reviews several THz circuits around 300 GHz developed in SKLMMW. Base on substrate integrated waveguide technology (SIW), cavities and filters are designed on commercial silicon based CMOS process. Measurement results of fabricated filter shows good performance at 280 GHz on on-chip measurement. Another approach uti-
realized the merit of high Q cavities using MEMS process and realized antenna and filter on it. Measurement result shows excellent performance at 350 GHz on quasi-optical test.

3.1 Silicon Based THz Filters on CMOS

THz filter is designed by utilizing substrate integrated waveguide technology on CMOS technology. The cavity of SIW is designed using the thick dielectric layers on the process structure, in which the top and bottom plane is utilized by cutting slots in the thick metal layer, in order to fulfill the requirements of the design rule. The cavities and filters are optimized with the process parameters.

A square resonant cavity filled with dielectric was firstly constructed on the chip. But the metallic layer is different from the usual SIW, since the metallic layers on chip cannot have a large size without a slot or a window. The design rules also require that the ratio of metal area to dielectric area fall in a given range. So the cavity has been designed with metallic layer modified, as shown in Fig. 18. The side wall is constructed by rows of via, which is similar to usual SIW cavities. The upper and lower metallic layer of cavity is a period contracture. The dielectric layer utilized the silicon oxide and nitride layer between MA and LY layer of IBM 130 nm CMOS process. In this cavity, the dominant mode TE101 could be simulated by eigen-mode method. The resonant frequency is found to be lower about 3% than usual cavity at 300 GHz. And the estimated Q value is about 60.

According the estimation, the cavity is suit for design filter with a fractional bandwidth great than 3%. A SIW filter and a half-mode SIW (HMSIW) filter based on CMOS is design and fabricated, as shown in Fig. 19 and Fig. 20. The size of HMSIW is around half the size of its counterpart SIW [7]–[11]. These two filter chips are measured using an on-chip measurement setup provide by the City University of Hong Kong. Only transmission data is retrieved from measurement because of the calibration problem in this setup. From the measured data in Fig. 21 and Fig. 22, the insertion loss of SIW and HMSIW filter is estimated lower than 5 dB if we take account of the SIW-microstrip transition loss and microstrip loss at each port.

3.2 Silicon Based THz Antenna and Filter on MEMS

A silicon based THz SIW bandpass filter is designed by using high Q cavities of MEMS process. In order to couple signals from quasi-optic test, a pair of linearly tapered slot antennas (ALTSA) are designed. The integrated antenna and filter are then fabricated with MEMS process and tested around 360 GHz.

Figure 23 shows the filter model based on CST software. It is a dual mode filter with circular cavities [12], [13]. Simulation shows very low insertion loss of the filter about 0.3 dB around 356 GHz, because of the high Q-factor (estimated 1000).

A pair of antennas must be connected at the input and output ports for a quasi-optic test setup. As shown in Fig. 24, a wideband ALTSA is chosen and a triangle taper is de-
signed as the transition between the filter input/output and ALTSA [14], [15].

An integrated prototype with passband range 350 GHz ~ 370 GHz is designed and fabricated with MEMS process, as shown in Fig. 25. It is measured by using a quasi-optic testing system. The measured data is in agreement with the simulated result, which shows the filter has good selection performance and verified the wideband characteristic of the ALTSAs, as shown in Fig. 26.

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References


Jixin Chen received the B.S. degree in radio engineering from Southeast University, Nanjing, China, in 1998, and the M.S. and Ph.D. degrees from Southeast University, Nanjing, China, in 2002 and 2006, respectively, all in electromagnetic field and microwave technique. Since 1998, he has been with the State Key Lab. of Millimeter Waves, Southeast University, and is currently an associate professor of the School of Information Science and Engineering. His current research interests include microwave and millimeter-wave circuit design and MMIC design. He has authored and co-authored more than 50 journal papers and presented invited papers at 2011 Global Symposium on Millimeter Waves (GSMM2011), 2010 NFSC–FQRNT 2010 workshop, 2011 China Microwave and Millimeter Wave Conference. He has served as TPC co-chairs of HSIC2012, UCMMT2012, session co-chair of APMC2007, ISSSE2010, iWAT2011, and reviewer for IEEE MWCL, APMC2008 and ICUWB2010, etc.

Wei Hong received the B.S. degree from the University of Information Engineering, Zhenzhou, China, in 1982, and the M.S. and Ph.D. degrees from Southeast University, Nanjing, China, in 1985 and 1988, respectively, all in radio engineering. Since 1988, he has been with the State Key Lab. of Millimeter Waves, Southeast University, and is currently a professor of the School of Information Science and Engineering. In 1993, 1995, 1996, 1997 and 1998, he was a short-term Visiting Scholar with the University of California at Berkeley and at Santa Cruz, respectively. He has been engaged in numerical methods for electromagnetic problems, microwave and millimeter wave theory and technology, RF and antenna technology for mobile communications etc. He has authored and co-authored over 200 technical publications, and authored two books of “Principle and Application of the Method of Lines” (in Chinese, Southeast University Press, 1993) and “Domain Decomposition Methods for Electromagnetic Problems” (in Chinese, Science Press, 2005). He twice awarded the first-class Science and Technology Progress Prizes issued by the Ministry of Education of China in 1992 and 1994 respectively, awarded the fourth-class National Natural Science Prize in 1991, and the first-, second- and third-class Science and Technology Progress Prizes of Jiangsu Province. Besides, he also received the Foundations for China Distinguished Young Investigators and for “Innovation Group” issued by NSF of China. Dr. Hong is a fellow of IEEE, senior member of CIE, Vice-Presidents of Microwave Society and Antenna Society of CIE, and served as the associate editor for IEEE Trans. on Microwave Theory and Technique, and reviewer for many technique journals of IEEE Trans. on MTT, on AP, IET Proc.-H, Electron. Lett. etc.

Hongjun Tang received the B.S. degree in radio engineering from the Sichuan Institute of Light Industry and Chemical Technology, Zigong, China, in 1992, the M.S. degree in circuits and system from the University of Electronic Science and Technology of China, Chengdu, China, in 2000, and the Ph.D. degree in electromagnetic field and microwave technology from the Southeast University, Nanjing, China. From 1992 to 2002 he worked in the Sichuan Institute of Light Industry and Chemical Technology. He has worked in the Southeast University since 2007. His research interests include microwave and millimeter wave component, circuits and system.

Pinpin Yan received the B.S. degree in radio engineering from Southeast University, Nanjing, China, in 2000, and the M.S. and Ph.D. degrees from Southeast University, Nanjing, China, in 2004 and 2009, respectively, all in electromagnetic field and microwave technique. Since 2000, she has been with the State Key Lab. of Millimeter Waves, Southeast University, and is currently an associate professor of the School of Information Science and Engineering. Her current research interests include microwave and millimeter-wave circuit design and MMIC design.

Li Zhang received the B.S. degree from Southeast University in 1997. She is currently a senior engineer of the Institute of RF- & OE-ICs, School of Information Science and Engineering, Southeast University. Her research interest is focused on the IC software platform and MPW projects.

Guangqi Yang received the B.S. degree in electronic engineering from Nanjing University of Aeronautics and Astronautics, China, in 1995 and the M.Sc. degree in electronic engineering from the Southeast University, China, in 2002. His main research interests concern architecture design of MIMO systems and passive components. His current research is about design and measurement for millimeter wave components and systems.
Debin Hou received the B.S. degree from the School of Physical Electronics, University of Electronic Science and Technology of China (UESTC), Chengdu China, in 2007. He is currently working toward the Ph.D. degree in the School of Information Science and Engineering, Southeast University (SEU), Najing China. He is now also with the Institute of Microelectronics (IME), Agency for Science, Technology and Research (A*STAR), Singapore, as an exchange student. His current research interests include millimeter-wave on-chip components, antennas and integrated circuits.

Ke Wu is currently a Professor of electrical engineering and Tier-I Canada Research Chair in RF and millimeter-wave engineering with the Ecole Polytechnique de Montreal, Montreal, QC, Canada. He also holds the first Cheung Kong endowed chair professorship (visiting) with Southeast University, the first Sir Yue-Kong Pao chair professorship (visiting) with Ningbo University, and an honorary professorship with the Nanjing University of Science and Technology and the City University of Hong Kong. He has been the Director of the Poly-Grames Research Center and the Director of the Center for Radiofrequency Electronics Research of Quebec (Regroupement stratégiq de FRQNT). He has authored or coauthored over 630 referred papers and a number of books/book chapters. He holds numerous patents. He has served on the editorial/review boards of many technical journals, transactions and letters, as well as scientific encyclopedias as both an Editor and Guest Editors. His current research interests involve substrate integrated circuits (SICs), antenna arrays, advanced computer-aided design (CAD) and modeling techniques, and development of low-cost RF and millimeter-wave transceivers and sensors for wireless systems and biomedical applications. He is also interested in the modeling and design of microwave photonic circuits and systems. Dr. Wu is a member of the Electromagnetics Academy, Sigma Xi, and the URSI. He is a Fellow of the Canadian Academy of Engineering (CAE) and the Royal Society of Canada (The Canadian Academy of the Sciences and Humanities). He has held key positions in and has served on various panels and international committees including the chair of Technical Program Committees, International Steering Committees, and international conferences/symposia. He will be the general chair of the 2012 IEEE Microwave Theory and Techniques Society (IEEE MTT-S) International Microwave Symposium (IMS). He is currently the chair of the joint IEEE chapters of the IEEE MTT-S/ Antennas and Propagation Society (AP-S)/Lasers and Electro-Optics Society (LEOS), Montreal, QC, Canada. He is an elected IEEE MTT-S Administrative Committee (AdCom) member for 2006-2009 and is the chair of the IEEE MTT-S Transnational Committee. He is an IEEE MTT-S Distinguished Microwave Lecturer (2009-2011). He was the recipient of many awards and prizes including the first IEEE MTT-S Outstanding Young Engineer Award and the 2004 Fessenden Medal of the IEEE Canada.